

IN THE CLAIMS:

1. (Original) A semiconductor device characterized by comprising
an embedded insulation layer formed in a semiconductor substrate;
a trench isolating between a plurality of power semiconductor elements
formed on the semiconductor substrate on said embedded insulation layer and
said power semiconductor elements; and
an isolator insulating and driving control electrodes of said power
semiconductor elements.
2. (Original) A semiconductor device according to claim 1,
characterized in that said plurality of power semiconductor elements are
connected in series and each has constant voltage elements connected in parallel.
3. (Original) A semiconductor device characterized by comprising
an embedded insulation layer formed in a semiconductor substrate;
a trench isolating between a plurality of power semiconductor elements
formed on the semiconductor substrate on said embedded insulation layer and
said power semiconductor elements; and
an isolator insulating and driving control electrodes of said power
semiconductor elements.

4-14. (Cancelled)